

[54] SILICON WAFER EMITTER ELECTRODE CONFIGURATION

3,319,139 5/1967 Rueffer ..... 357/68 X  
3,821,780 6/1974 Harland, Jr. et al. .... 357/68 X

[76] Inventor: Winton C. Strumpell, 6027 Corning Ave., Los Angeles, Calif. 90056

Primary Examiner—Susan J. Lucas  
Attorney, Agent, or Firm—Warren T. Jessup

[\*\*] Term: 14 Years

[57] CLAIM

[21] Appl. No.: 957,770

The ornamental design for a silicon wafer emitter electrode configuration, substantially as shown and described.

[22] Filed: Nov. 3, 1978

DESCRIPTION

[51] Int. Cl. .... D13—99

[52] U.S. Cl. .... D13/99

[58] Field of Search ..... 437/77, 88, 93; 357/68, 357/70; D13/99

FIG. 1 is a top plan view of a silicon wafer emitter electrode configuration showing my new design.

FIGS. 2 and 3 are end and side elevational views respectively of the electrode configuration.

This is a design for the characteristic features of emitter electrode configurations deposited on a silicon wafer with the electrodes delineated by the black areas in FIG. 1. The wafer is shown in broken lines for illustration purposes only.

[56] References Cited

U.S. PATENT DOCUMENTS

2,707,762 5/1955 Stuetzer ..... 357/68 X  
3,301,706 1/1967 Flaschen et al. .... 427/93 X

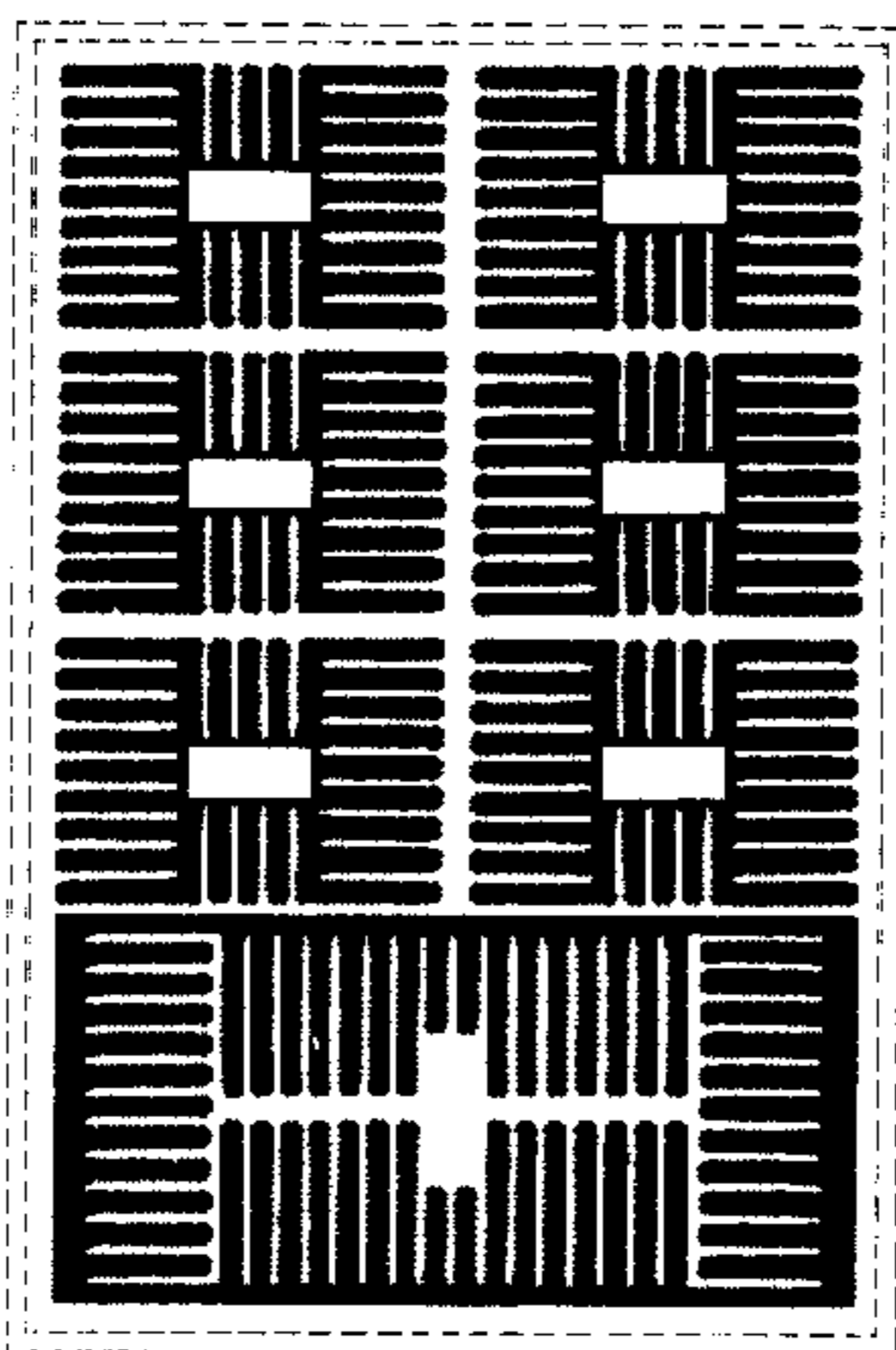


Fig. 2.

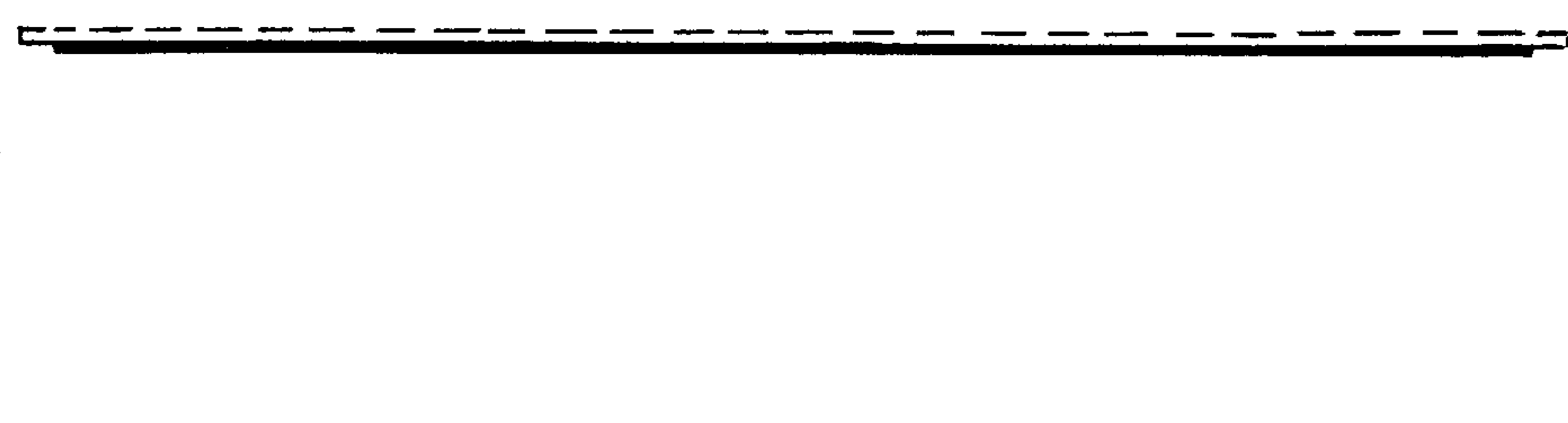


Fig. 1.

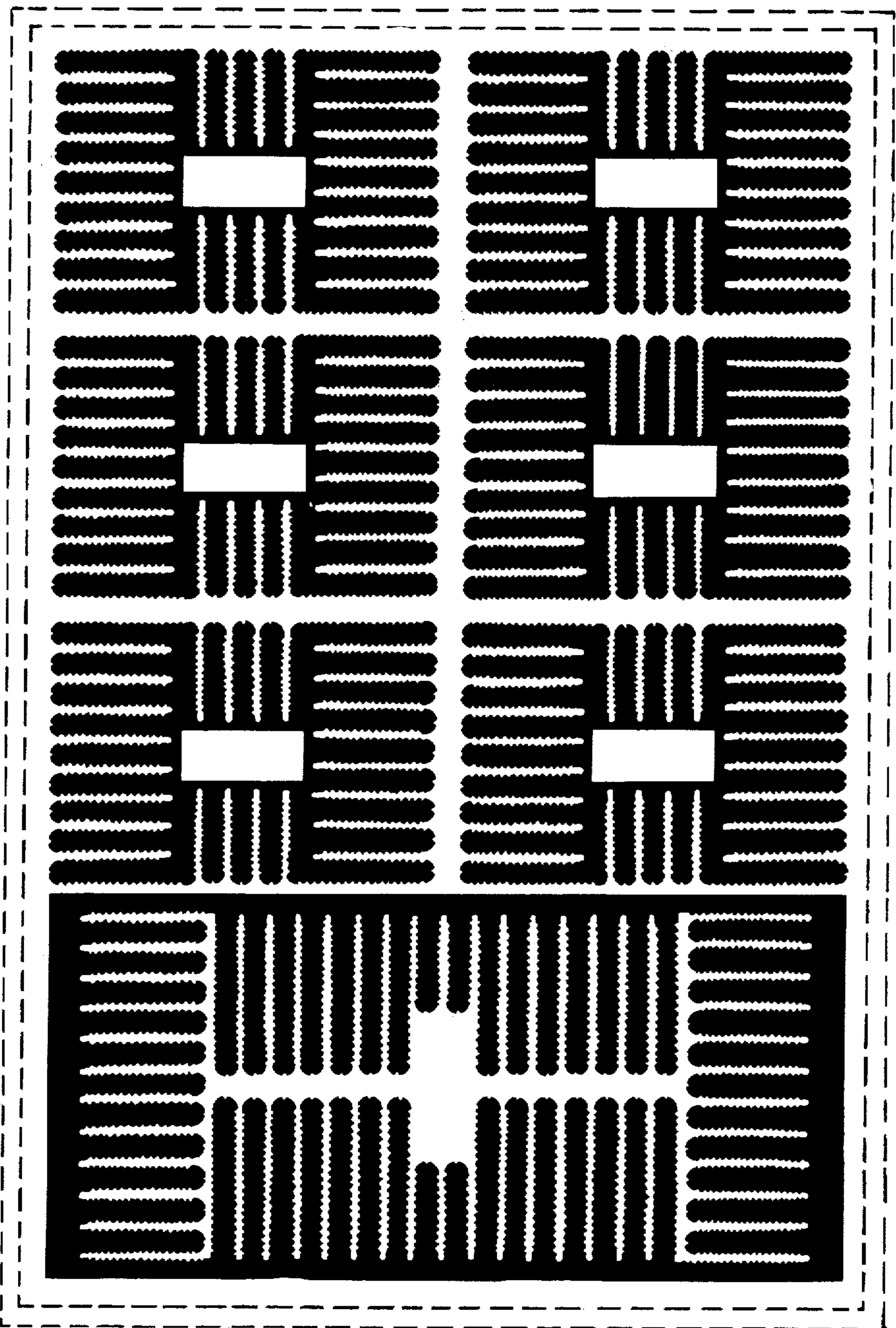


Fig. 3.

